



2N90

Power MOSFET

2A, 900V N-CHANNEL POWER MOSFET

■ DESCRIPTION

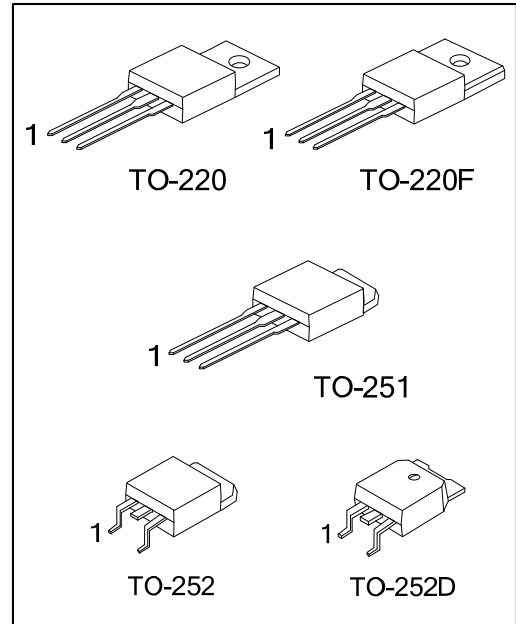
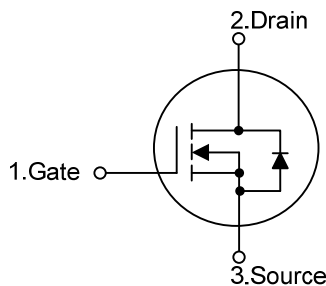
The UTC **2N90** is an N-channel mode power MOSFET using UTC's advanced technology to provide costumers with planar stripe and DMOS technology. This technology specialized in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **2N90** is universally applied in high efficiency switch mode power supply.

■ FEATURES

- * $R_{DS(ON)} < 7.2\Omega @ V_{GS}=10V, I_D=1.1A$
- * High switching speed
- * Improved dv/dt capability
- * 100% avalanche tested

■ SYMBOL



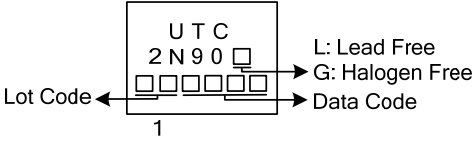
■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | Packing |
|-----------------|--------------|---------|----------------|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 2N90L-TA3-T | 2N90G-TA3-T | TO-220 | G | D | S | Tube |
| 2N90L-TF3-T | 2N90G-TF3-T | TO-220F | G | D | S | Tube |
| 2N90L-TM3-T | 2N90G-TM3-T | TO-251 | G | D | S | Tube |
| 2N90L-TN3-R | 2N90G-TN3-R | TO-252 | G | D | S | Tape Reel |
| 2N90L-TND-R | 2N90G-TND-R | TO-252D | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|--|--|
| <p>2N90L-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p> | <p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TM3: TO-251, TN3: TO-252, TND: TO-252D (3) L: Lead Free, G: Halogen Free and Lead Free</p> |
|--|--|

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|------------------------------------|------------------------|-----------|----------|------------------|
| Drain-Source Voltage (Note 2) | | V_{DSS} | 900 | V |
| Gate-Source Voltage | | V_{GSS} | ± 30 | V |
| Drain Current | Continuous | I_D | 2.2 | A |
| | Pulsed (Note 2) | I_{DM} | 8.8 | A |
| Avalanche Current (Note 2) | | I_{AR} | 2.2 | A |
| Avalanche Energy | Single Pulsed (Note 3) | E_{AS} | 170 | mJ |
| | Repetitive (Note 2) | E_{AR} | 8.5 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 4.0 | V/ns |
| Power Dissipation | TO-220 | P_D | 85 | W |
| | TO-220F | | 25 | |
| | TO-251/ TO-252 | | 43 | |
| | TO-252D | | | |
| Junction Temperature | | T_J | +150 | $^\circ\text{C}$ |
| Storage Temperature | | T_{STG} | -55~+150 | $^\circ\text{C}$ |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 65\text{mH}$, $I_{AS} = 2.2\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 2.2\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

| PARAMETER | PACKAGE | SYMBOL | RATINGS | UNIT |
|---------------------|----------------|---------------|---------|---------------------------|
| Junction to Ambient | TO-220/TO-220F | θ_{JA} | 62.5 | $^\circ\text{C}/\text{W}$ |
| | TO-251/ TO-252 | | 110 | |
| | TO-252D | | | |
| Junction to Case | TO-220 | θ_{JC} | 1.47 | $^\circ\text{C}/\text{W}$ |
| | TO-220F | | 5 | |
| | TO-251/ TO-252 | | 2.85 | |
| | TO-252D | | | |

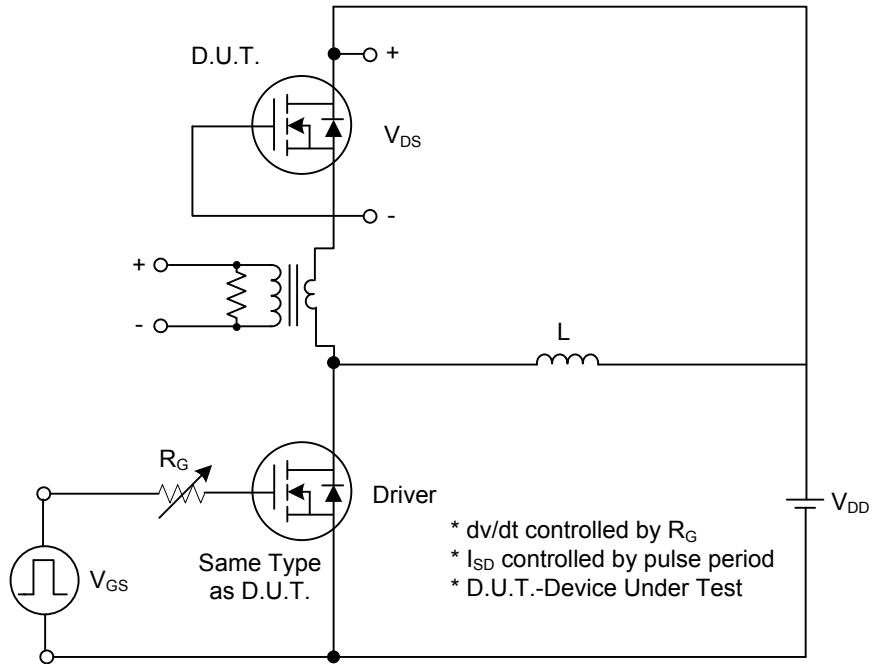
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|---------|------------------------------|--|-----|-----|------|---------------------------|
| OFF CHARACTERISTICS | | | | | | | |
| Drain-Source Breakdown Voltage | | BV_{DSS} | $I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$ | 900 | | | V |
| Breakdown Voltage Temperature Coefficient | | $\Delta BV_{DSS}/\Delta T_J$ | Reference to 25°C , $I_D=250\mu\text{A}$ | | 1.0 | | $\text{V}/^\circ\text{C}$ |
| Drain-Source Leakage Current | | I_{DSS} | $V_{DS}=900\text{V}$, $V_{GS}=0\text{V}$ | | | 10 | μA |
| | | | $V_{DS}=720\text{V}$, $T_C=125^\circ\text{C}$ | | | 100 | |
| Gate- Source Leakage Current | Forward | I_{GSS} | $V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$ | | | +100 | nA |
| | Reverse | | $V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$ | | | -100 | nA |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$ | 3.0 | | 5.0 | V |
| Static Drain-Source On-State Resistance | | $R_{DS(ON)}$ | $V_{GS}=10\text{V}$, $I_D=1.1\text{A}$ | | 5.6 | 7.2 | Ω |
| Forward Transconductance | | g_{FS} | $V_{DS}=50\text{V}$, $I_D=1.1\text{A}$ (Note 1) | | 2.0 | | S |
| DYNAMIC PARAMETERS | | | | | | | |
| Input Capacitance | | C_{ISS} | $V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$ | | 480 | 520 | pF |
| Output Capacitance | | C_{OSS} | | | 45 | | |
| Reverse Transfer Capacitance | | C_{RSS} | | | 7 | | |
| SWITCHING PARAMETERS | | | | | | | |
| Turn-ON Delay Time | | $t_{D(ON)}$ | $V_{GS}=10\text{V}$, $V_{DD}=30\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1,2) | | 50 | | ns |
| Rise Time | | t_R | | | 65 | | |
| Turn-OFF Delay Time | | $t_{D(OFF)}$ | | | 90 | | |
| Fall-Time | | t_F | | | 45 | | |
| Total Gate Charge | | Q_G | $V_{GS}=10\text{V}$, $V_{DS}=50\text{V}$, $I_D=1.3\text{A}$ $I_G=100\mu\text{A}$ (Note 1,2) | | 16 | 26 | nC |
| Gate to Source Charge | | Q_{GS} | | | 5.5 | | |
| Gate to Drain Charge | | Q_{GD} | | | 4.5 | | |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | | I_S | | | | 2.2 | A |
| Maximum Pulsed Drain-Source Diode Forward Current | | I_{SM} | | | | 8.8 | A |
| Drain-Source Diode Forward Voltage | | V_{SD} | $I_S=2.2\text{A}$, $V_{GS}=0\text{V}$ | | | 1.4 | V |
| Reverse Recovery Time | | t_{rr} | $I_S=2.2\text{A}$, $V_{GS}=0\text{V}$, $dI_F/dt=100\text{A}/\mu\text{s}$ | | 400 | | ns |
| Reverse Recovery Charge | | Q_{RR} | s (Note 1) | | 1.6 | | μC |

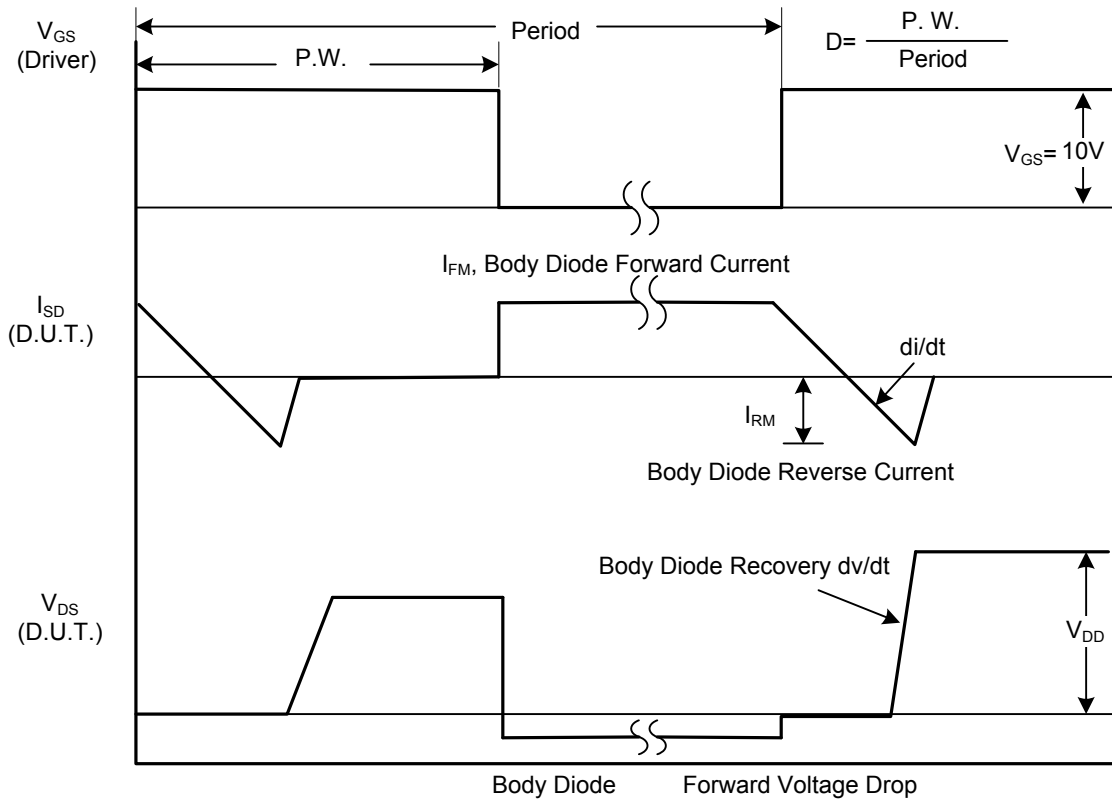
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

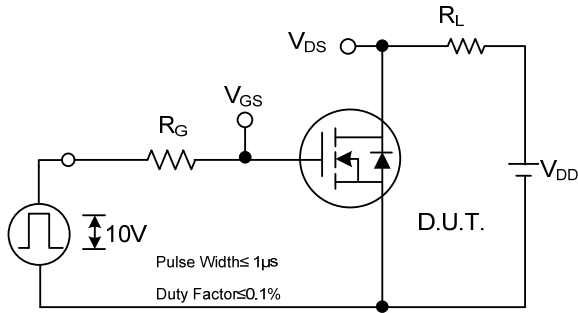


Peak Diode Recovery dv/dt Test Circuit

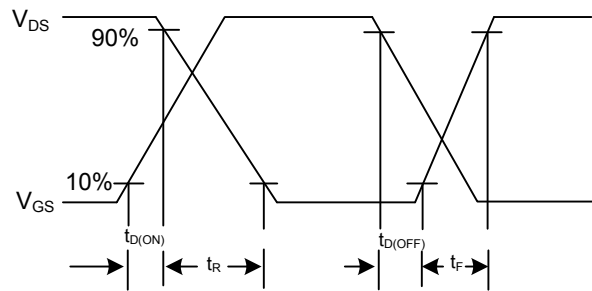


Peak Diode Recovery dv/dt Waveforms

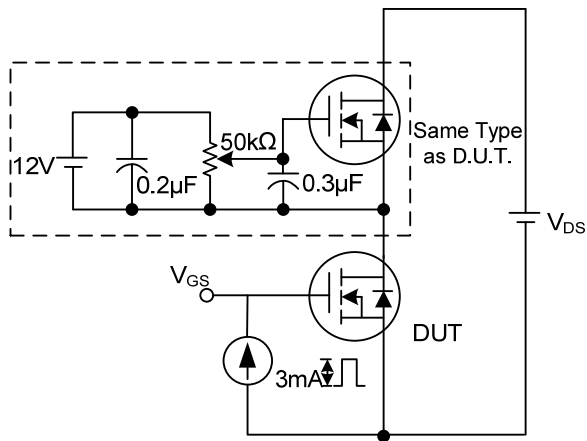
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



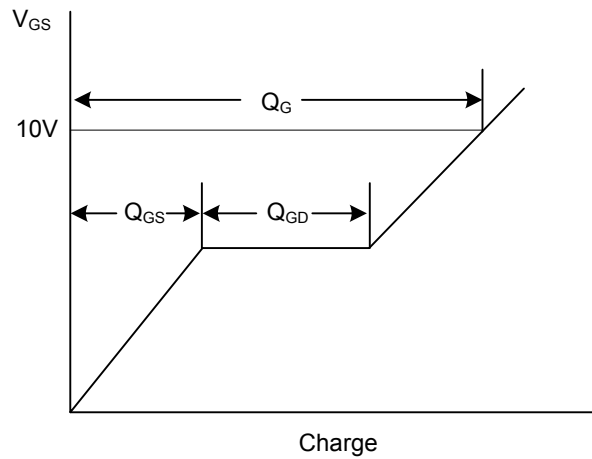
Switching Test Circuit



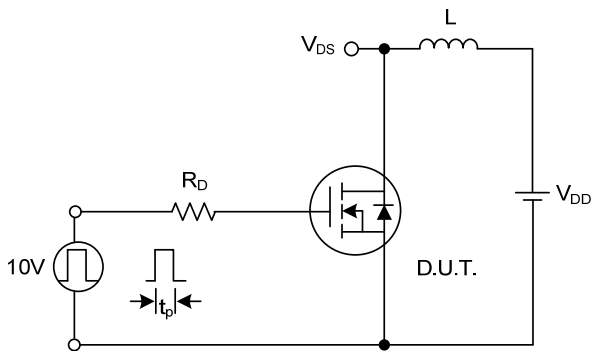
Switching Waveforms



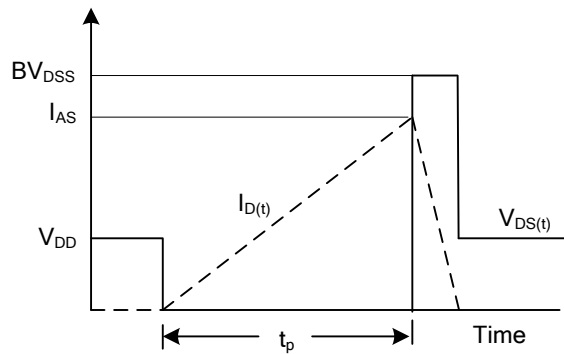
Gate Charge Test Circuit



Gate Charge Waveform

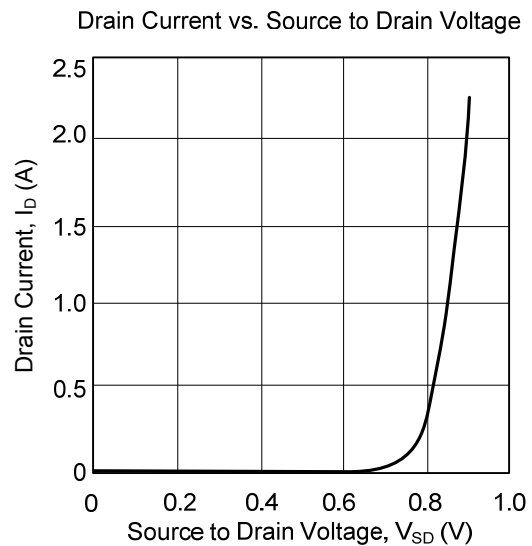
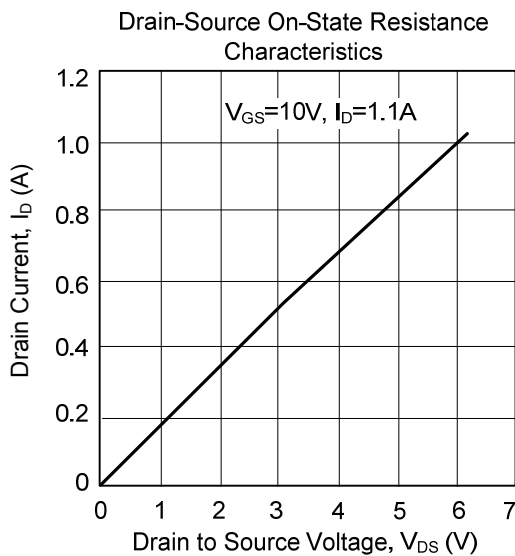
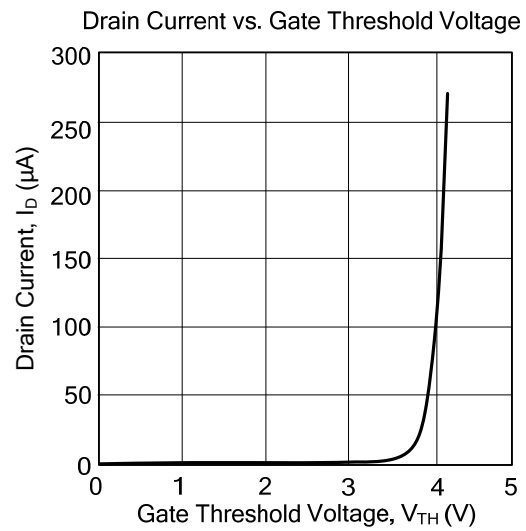
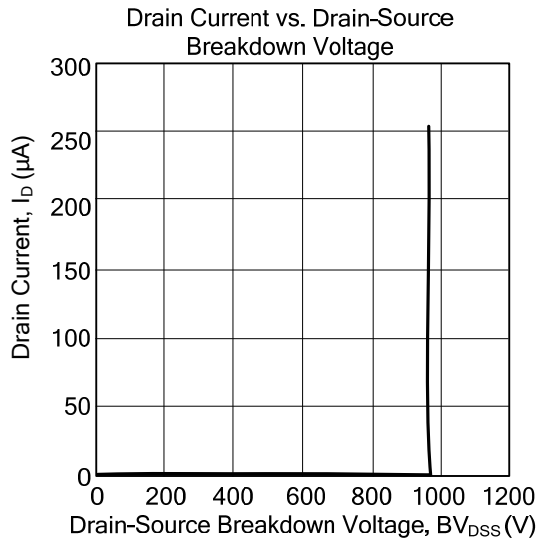


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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